L Number	Hits	Search Text	DB	Time stamp
1	41	(ferroelectric ferro-electric FeRAM) and	USPAT;	2003/05/19
		(program\$4 writ\$3) and (chang\$3 with polar\$7 with (volt\$3 near3 gate))	US-PGPUB; EPO; JPO; DERWENT;	15:47
2	8	<pre>(ferroelectric ferro-electric FeRAM) and ((program\$4 writ\$3) same (chang\$3 with polar\$7 with (film layer) with (volt\$3 near3 gate)))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/19 15:48
-	207	(mfs MFMIS) with (ferroelectric ferro-electric)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05
-	109	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/06 16:59
-	12	<pre>(((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:58
-	14498	(mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:06
-	3093	((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:08
-	29	(((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 12:55
_	18496	(mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 13:07
_	3302	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 13:09
_	29	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/06 16:58
-	10	<pre>(((mfs MFIS MFMIS) (metal adj3   (ferroelectric ferro-electric) adj3   insulator)) and (writ\$3 program\$4) and   (read\$3)) and ((current adj3 chang\$3)   same (Vds voltage)) and (ferroelectric adj3 capacitor)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55
-	10	((((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)) and (gate adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55

Search History 5/19/03 4:39:08 PM Page 1

-	4	, , , ,	USPAT;	2002/06/06
		(ferroelectric ferro-electric) adj3	US-PGPUB;	17:00
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		same (Vds voltage)) and ((ferroelectric	IBM_TDB	
		adj3 capacitor) with (gate adj3		
	205	electrode))		
-	205	((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
		(gate adj3 electrode))	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
_	40	(((ferroelectric adj3 capacitor) with	IBM_TDB USPAT;	2002/06/06
	10	(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	2002/06/06
		MFMIS)	EPO; JPO;	10.30
Ì			DERWENT;	İ
			IBM TDB	
-	32	((((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
		MFMIS)) and (writ\$3 program\$4) and	EPO; JPO;	17.00
		(read\$3)	DERWENT;	
			IBM TDB	
-	16	(((((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
		MFMIS)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((ferroelectric	DERWENT;	
		ferro-electric) adj3 insulator)	IBM TDB	
-	5690	read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
		with drain with source)	US-PGPUB;	11:17
•			EPO; JPO;	
			DERWENT;	
	574		IBM_TDB	
-	574	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)	US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
_	22	(((unsaturat\$3 non-saturat\$3) near3	IBM_TDB USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:19
		(nonvolatile non-volatile)	EPO; JPO;	11:19
		(	DERWENT;	
			IBM TDB	
-	2835	(read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
		with drain with source)) and (nonvolatile	US-PGPUB;	11:20
		non-volatile)	EPO; JPO;	1 - 1 - 2 - 3
			DERWENT;	
	1		IBM TDB	
-	5	((((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:23
		(nonvolatile non-volatile)) and ((read\$3	EPO; JPO;	
	]	same ((voltage potential bias) with drain	DERWENT;	
1		with source)) and (nonvolatile	IBM_TDB	
	10463	non-volatile))	-	
-	124614	((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile nonvolatile	US-PGPUB;	11:25
	[	nonvoiatile	EPO; JPO;	
	[		DERWENT;	
1_	22	(((unsaturat\$3 non-saturat\$3) near3	IBM_TDB	2002/02/20
	~~	region) and (saturat\$3 near3 region)) and	USPAT;	2003/03/20
		(((MFS MFMIS ferroelectric) near3	US-PGPUB;	11:25
		transistor) FeRAM non-volatile	EPO; JPO; DERWENT;	
		nonvolatile)	IBM TDB	
-	1	((((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		(((MFS MFMIS ferroelectric) near3	EPO; JPO;	*****
1	'			
	'	transistor) FeRAM non-volatile		
	,	transistor) FeRAM non-volatile nonvolatile)) and ((read\$3 with data with	DERWENT;	
	,	transistor) FeRAM non-volatile		

-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		((read\$3 with data with (appl\$3 near3	EPO; JPO;	
		<pre>(voltage bias potential)) with source with drain))</pre>	DERWENT;	
	224		IBM_TDB	2002/02/20
_	224	(voltage bias potential)) with source	USPAT; US-PGPUB;	2003/03/20
		with drain)	EPO; JPO;	11:30
		with drain,	DERWENT;	
			IBM TDB	
_	181	(((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
Ì	1	transistor) FeRAM non-volatile	US-PGPUB;	12:16
	İ	nonvolatile) and ((read\$3 with data with	EPO; JPO;	12.10
		(appl\$3 near3 (voltage bias potential))	DERWENT;	l i
		with source with drain))	IBM TDB	
_	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:29
		((((MFS MFMIS ferroelectric) near3	EPO; JPO;	
		transistor) FeRAM non-volatile	DERWENT;	
		nonvolatile) and ((read\$3 with data with	IBM_TDB	
		(appl\$3 near3 (voltage bias potential))		
		with source with drain)))		
-	1669	read\$3 same ((appl\$3 near3 (voltage bias	USPAT;	2003/03/20
		potential)) with source with drain)	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
	3	///wmgstumst63 man saturat63)3	IBM_TDB	2002/02/20
-	3	(((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and	USPAT; US-PGPUB;	2003/03/20
		(read\$3 same ((appl\$3 near3 (voltage bias	•	11:45
		potential)) with source with drain))	EPO; JPO; DERWENT;	
		potential), with source with dialily,	IBM TDB	.
_	11	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) with read\$3	US-PGPUB;	11:53
		legion, with readys	EPO; JPO;	11.55
			DERWENT;	
			IBM TDB	
-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) with read\$3) and (non-volatile	US-PGPUB;	11:52
	1	nonvolatile)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3769	(unsaturat\$3 non-saturat\$3) with read\$3	USPAT;	2003/03/20
			US-PGPUB;	11:53
			EPO; JPO;	
	1		DERWENT;	
_	2770	/ungatumate2 man	IBM_TDB	2002/02/22
-	3779	<pre>(unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3</pre>	USPAT;	2003/03/20
		with readys	US-PGPUB;	11:53
	1		EPO; JPO; DERWENT;	
			IBM TDB	
_	200	((unsaturat\$3 non-saturat\$3 nonsaturat\$3)	USPAT;	2003/03/20
		with read\$3) and (non-volatile	US-PGPUB;	11:54
		nonvolatile)	EPO; JPO;	
	}		DERWENT;	
			IBM TDB	
-	200	(((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
	·	transistor) FeRAM non-volatile	US-PGPUB;	12:04
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))	IBM_TDB	
-	28	((((MFS MFMIS ferroelectric) near3	USPĀT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	•
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM_TDB	
	L	(read reading)		

<u> </u>	8	((((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM TDB	
		(read reading)) and memory	_	
_	1	((read\$3 with data with (appl\$3 near3	USPAT;	2003/03/20
		(voltage bias potential)) with source	US-PGPUB;	12:19
		with drain)) and ((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) near3 region)	DERWENT;	
			IBM_TDB	
-	1	read\$3 with (unsaturat\$3 non-saturat\$3	USPAT;	2003/03/20
		nonsaturat\$3) with (current near3	US-PGPUB;	12:20
	ł	detect\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	